

isc Silicon NPN Power Transistors

2SD188

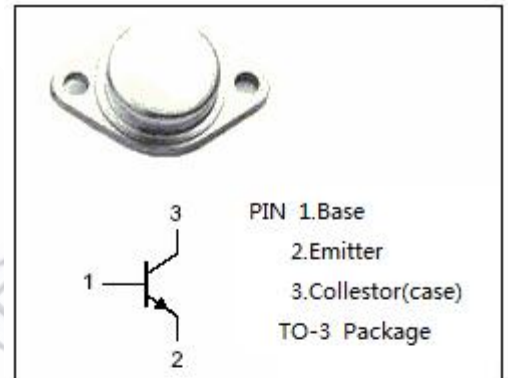
DESCRIPTION

With TO-3 package

- Large current capability
- Wide area of safe operation

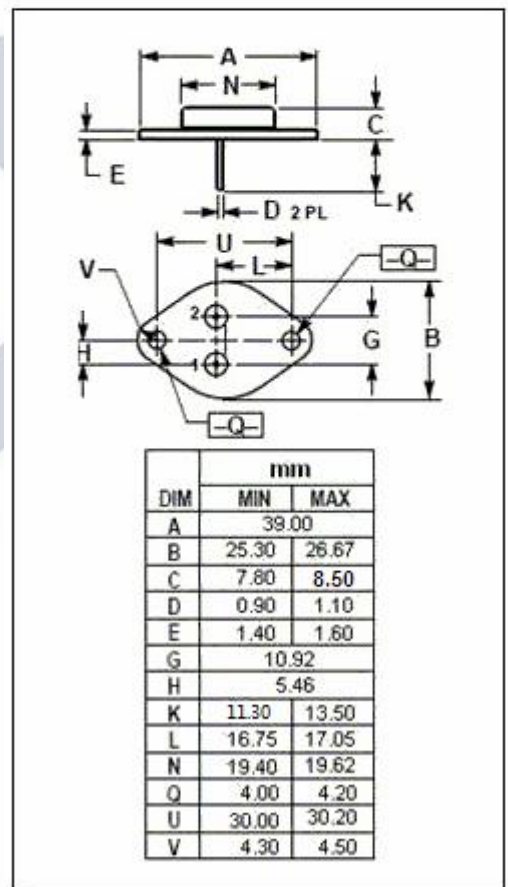
APPLICATIONS

- For audio frequency output applications



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	6	V
I _c	Collector Current-Continuous	7	A
P _c	Collector Power Dissipation @T _c =75°C	60	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



isc Silicon NPN Power Transistors**2SD188****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =0.5A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =2V	30		120	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		10		MHz